

# Oxides grown by Atomic Layer Deposition for applications in electronics, optoelectronics, biology and medicine

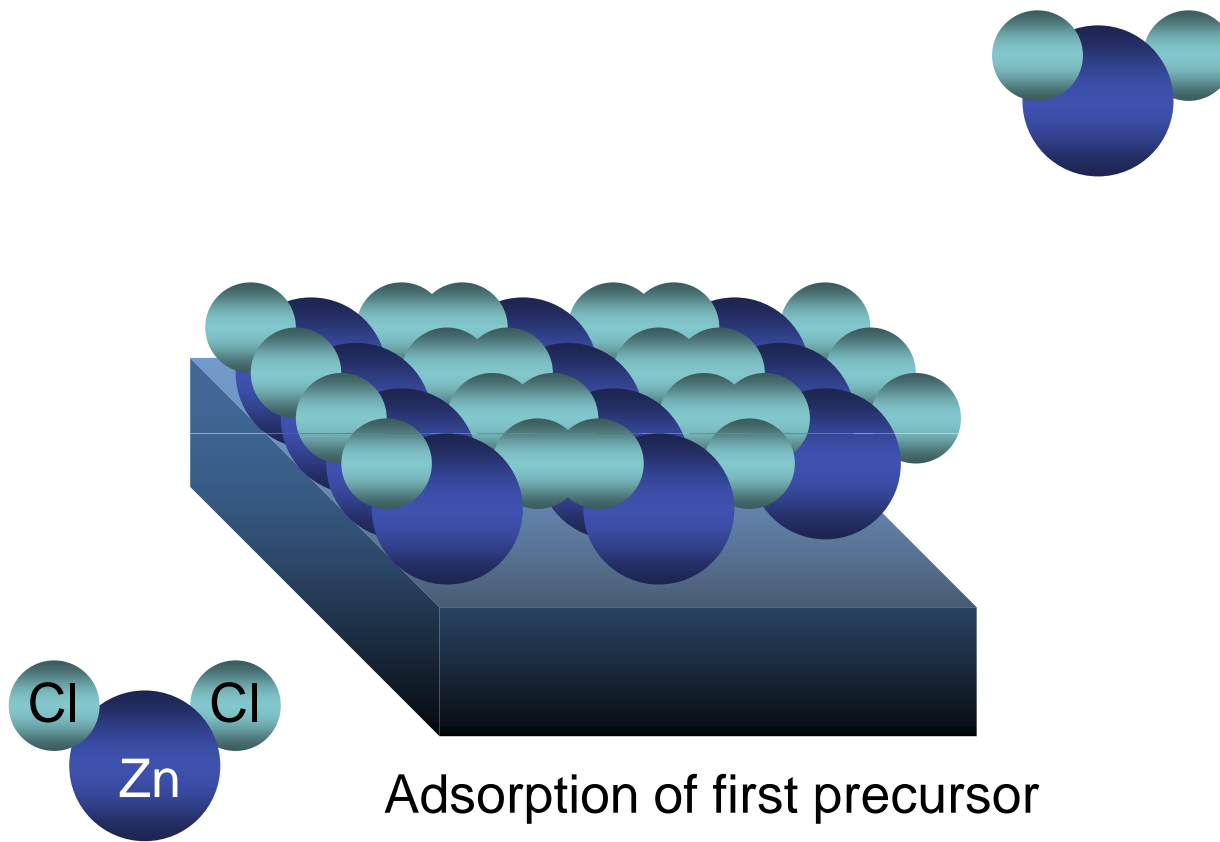
## Marek Godlewski

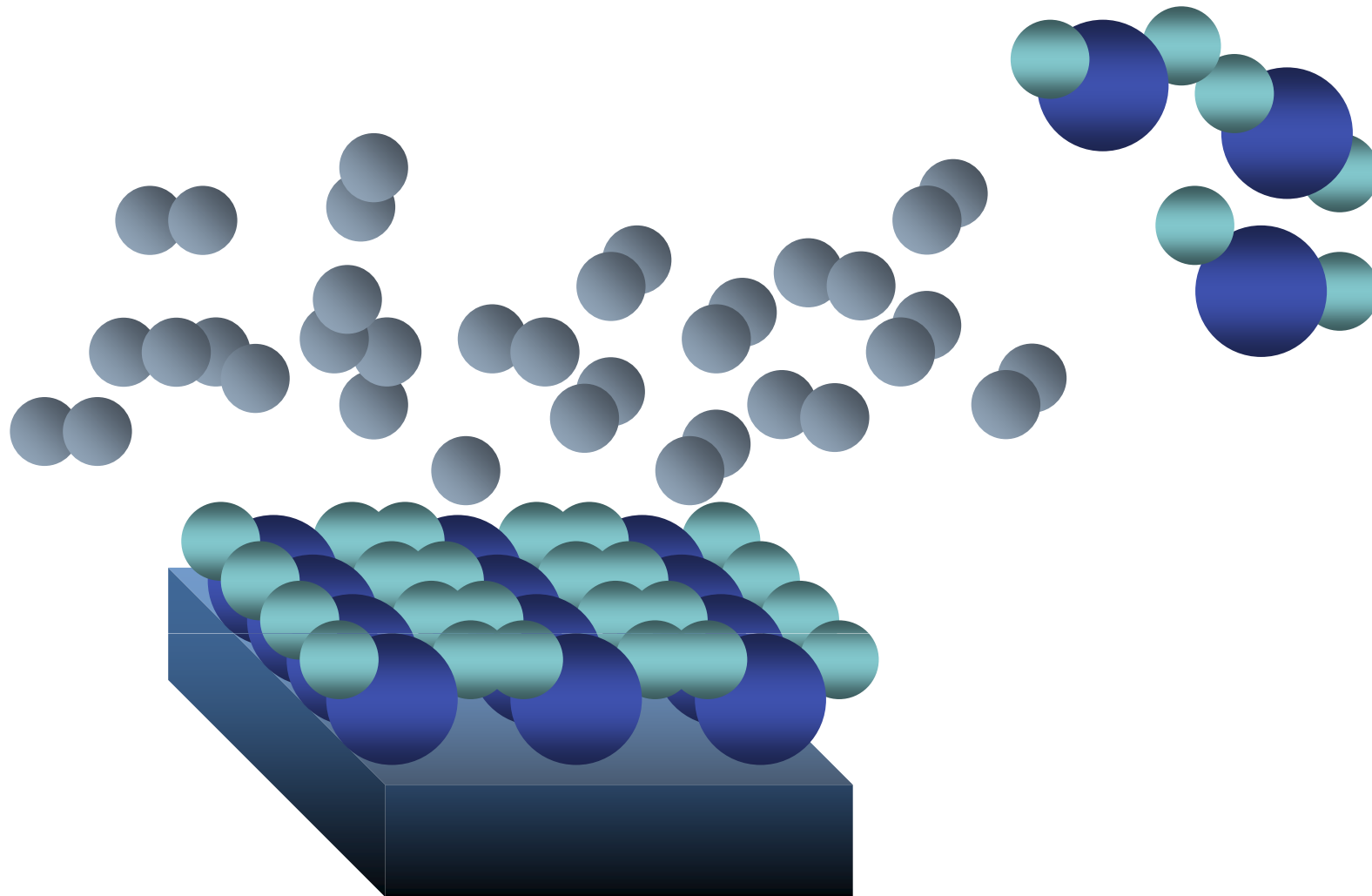
*Institute of Physics Polish Academy of Sciences,  
Al. Lotników 32/46, 02-668 Warsaw, Poland*



# ALD growth process



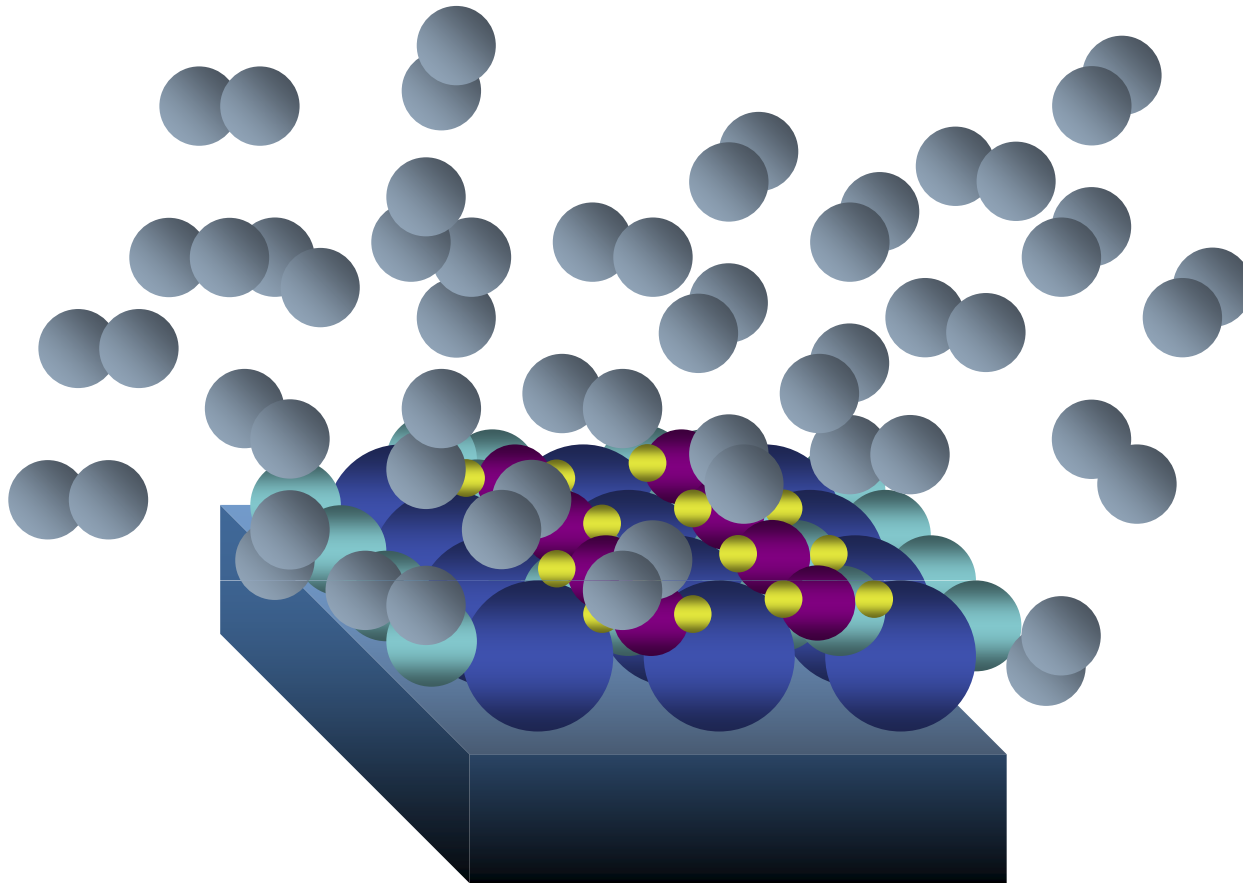




N

Surface saturation followed by reactor purging





## CVD

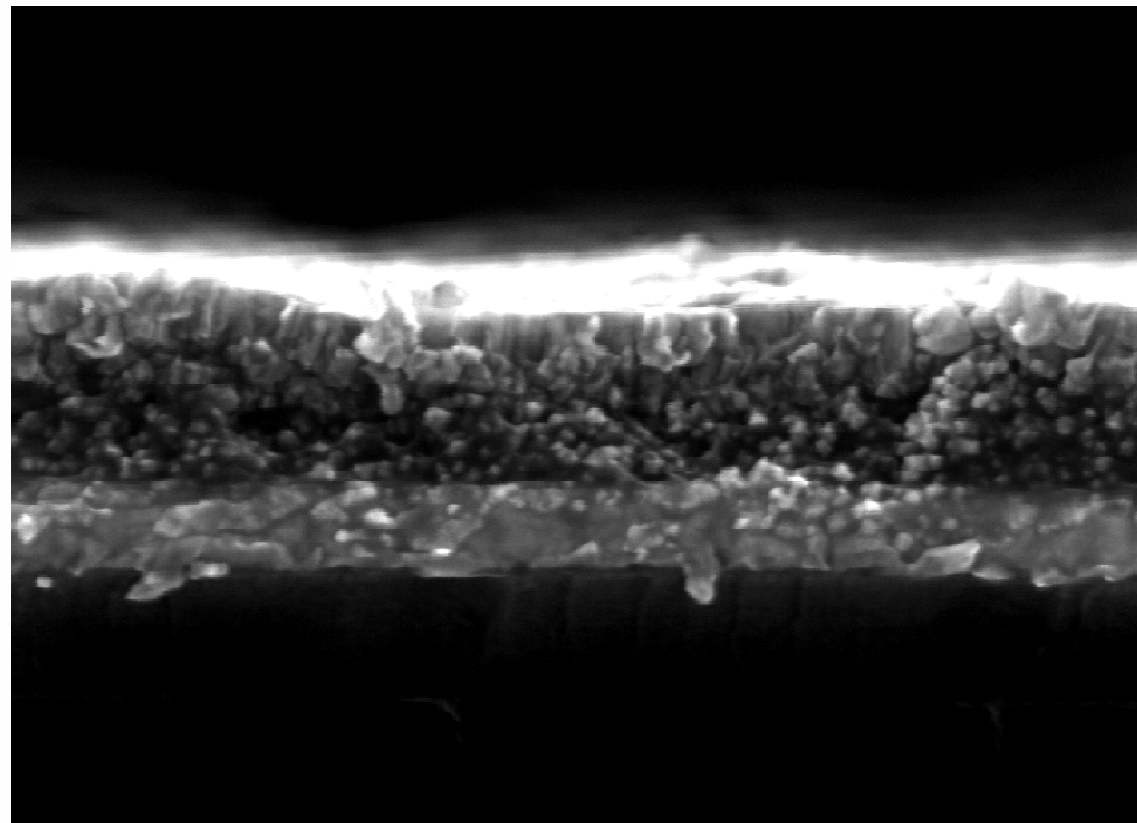
- Less reactive precursors
- Precursors react at the substrate but also before deposition
- Precursors can decompose at process temperature
- Uniformity requires uniform flux reactant and temperature
- Thickness control by precise process control and monitoring

## ALD

- Highly reactive precursors possible
- Precursors react only on the substrate of the film
- Precursors must not decompose at process temperature
- High uniformity of coating ensured by the saturation mechanism
- Good thickness control by selecting the number of ALD cycles
- Uniform doping of the layers possible
- Reactor scaling possible
- Multisubstrate deposition possible



# Benefits of the LT growth – Hybrid structures

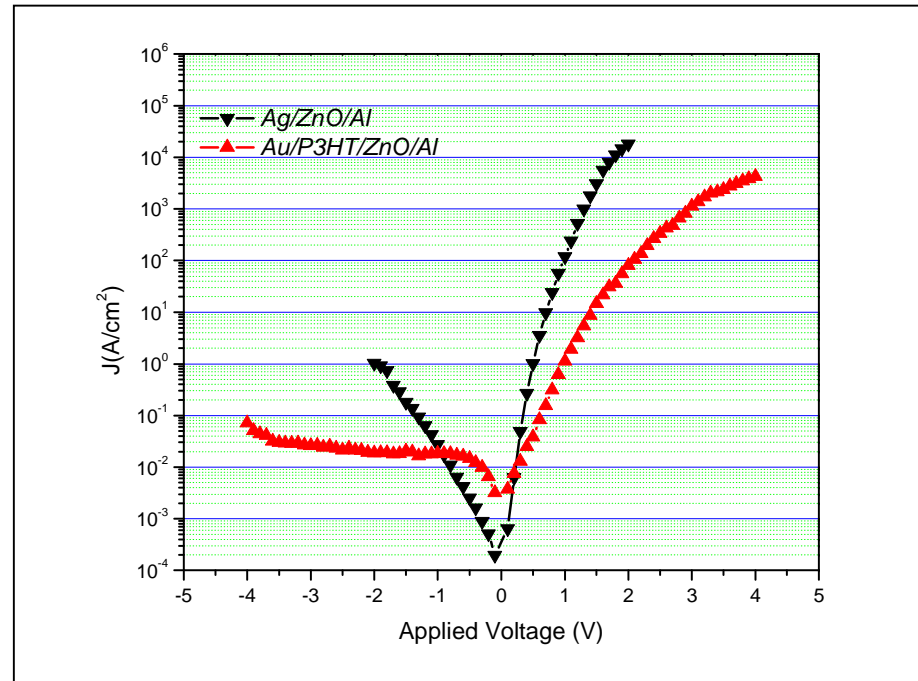


ZnO  
P3HT  
Au

Mag = 349.13 K X 200nm WD = 2 mm EHT = 15.00 kV Signal A = InLens Date :26 Feb 2008 Time :15:50:03  
SUPRA 40-25-45 Noise Reduction = Pixel Avg Extractor I = 123.00  $\mu$ A



# Electrical Characterization



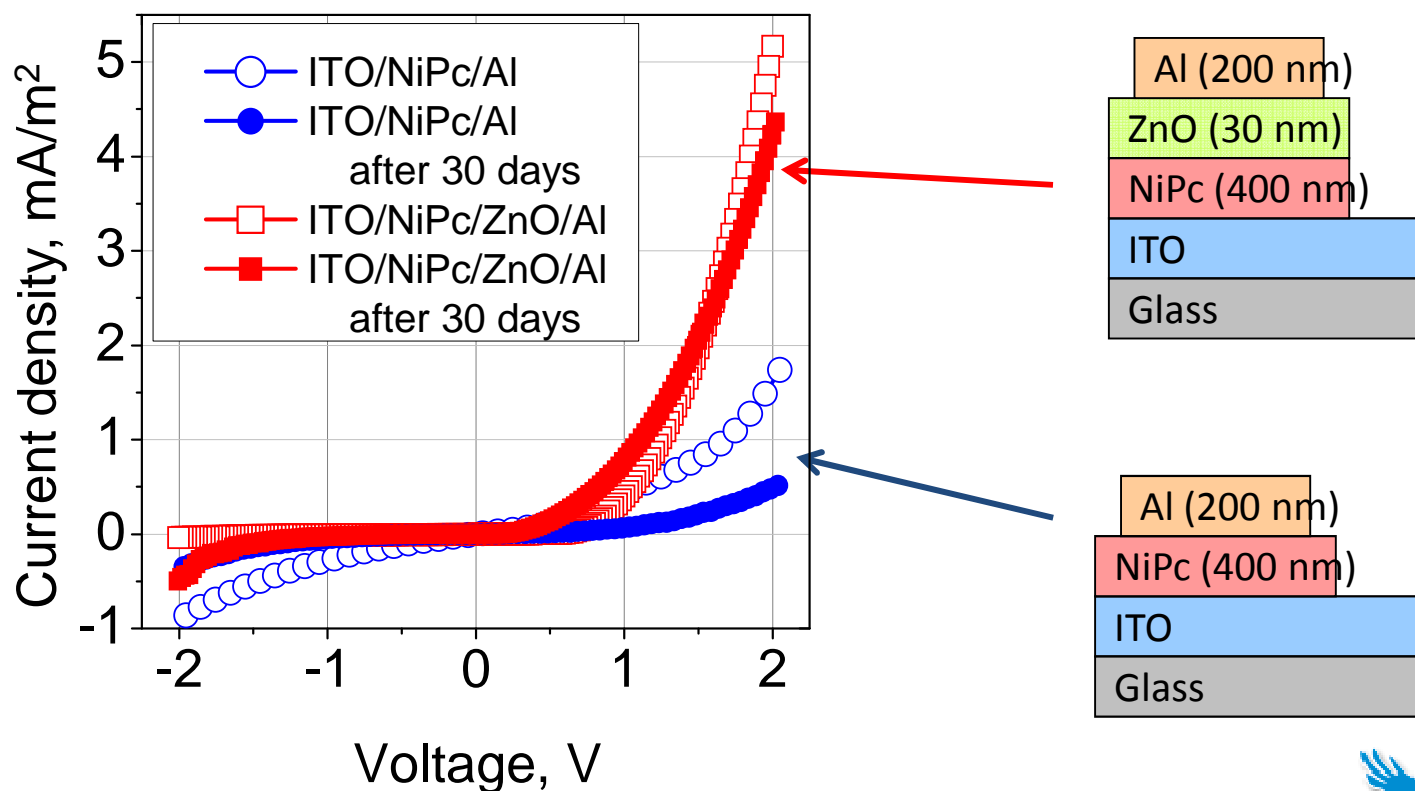
- **Improved junction behavior in terms of  $I_{\text{off}}$**
- $I_{\text{on}}/I_{\text{off}} \sim 10^5$ ,  $I_{\text{on}}/I_{\text{off}}$
- **High current density:  $J = 10^4 \text{ A}/\text{cm}^2$  at 4V ( $J = 0.02 \text{ A}/\text{cm}^2$  for a P3HT diode)**





# Photovoltaic diode based on ZnO/NiPc junction

## Effect of ZnO layer on device stability



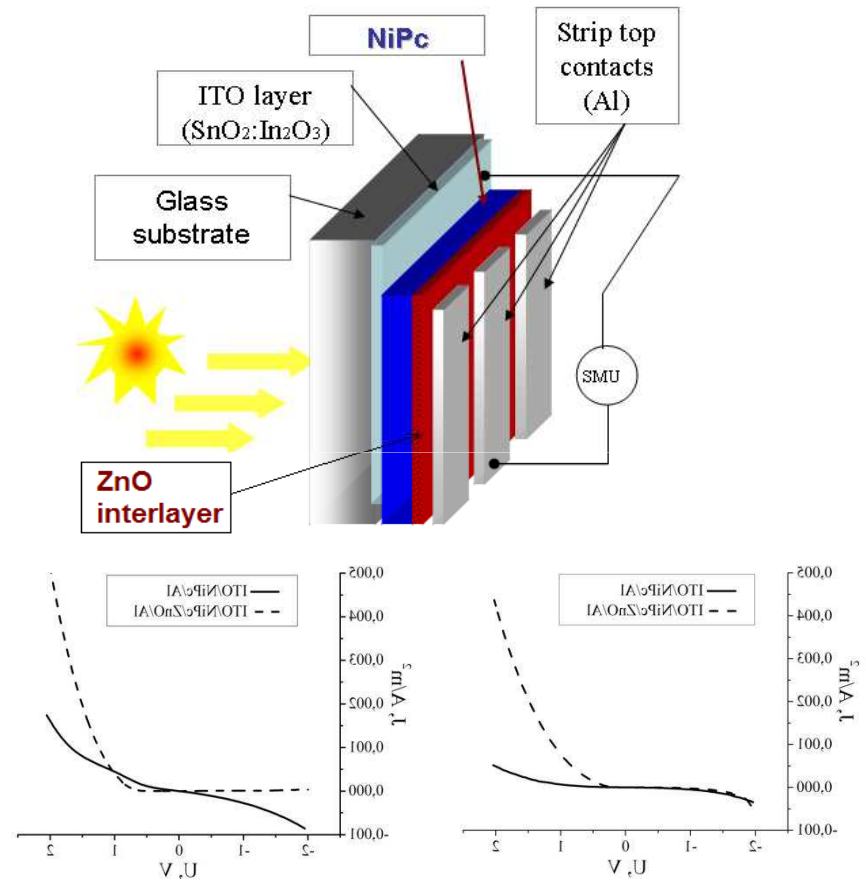
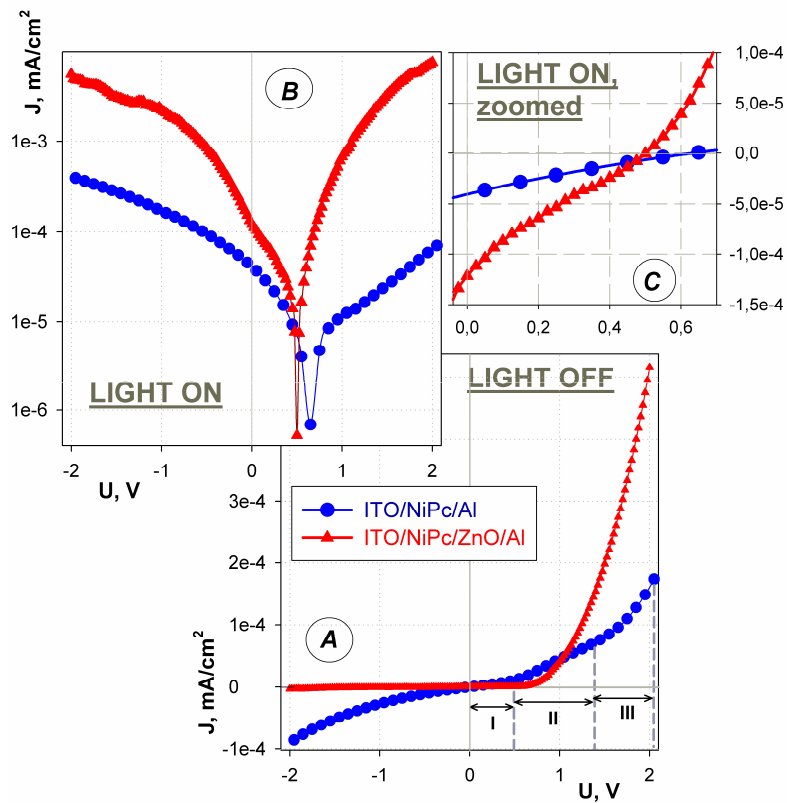
G. Łuka



Mat. Sci. Eng. B **172**, 272 (2010).



# Time stability



As prepared

After 30 days

G. Łuka



# Advantages of LT growth



# Transparent electronics



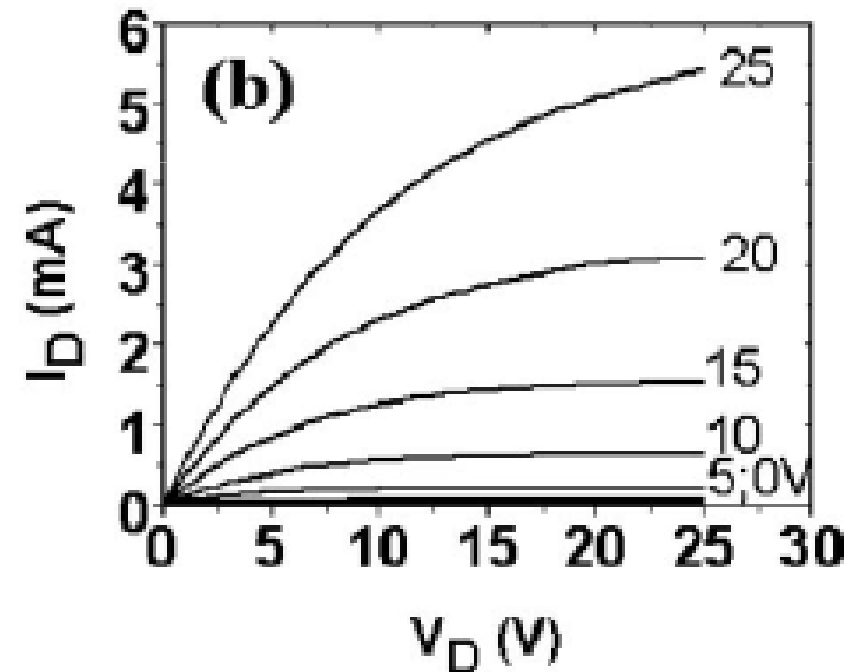
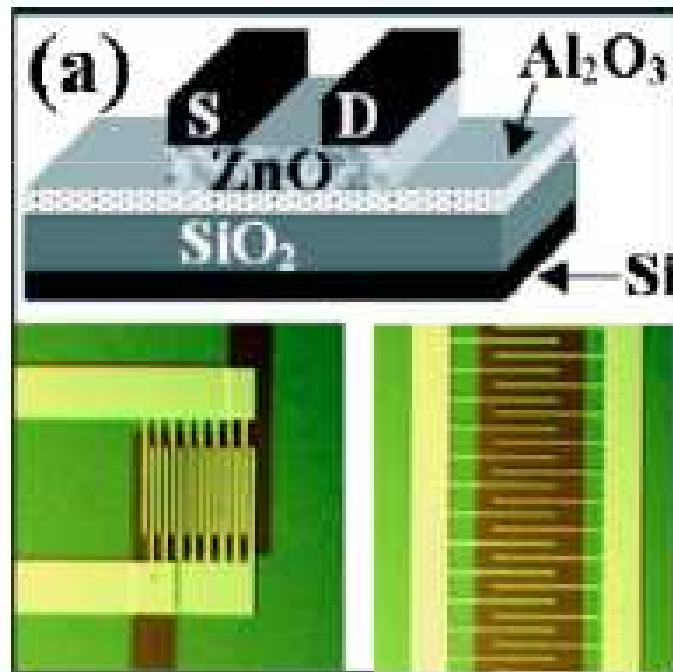
## Electrical behavior of zinc oxide layers grown by low temperature atomic layer deposition

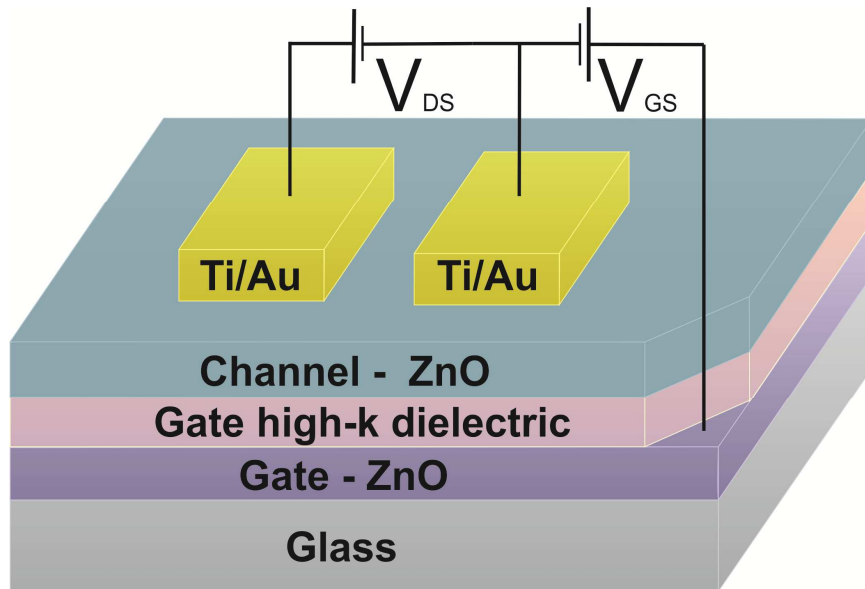
N. Huby<sup>a)</sup> and S. Ferrari

*MDM-INFM, 2 via camillo Olivetti, 20041 Agrate Brianza, Italy*

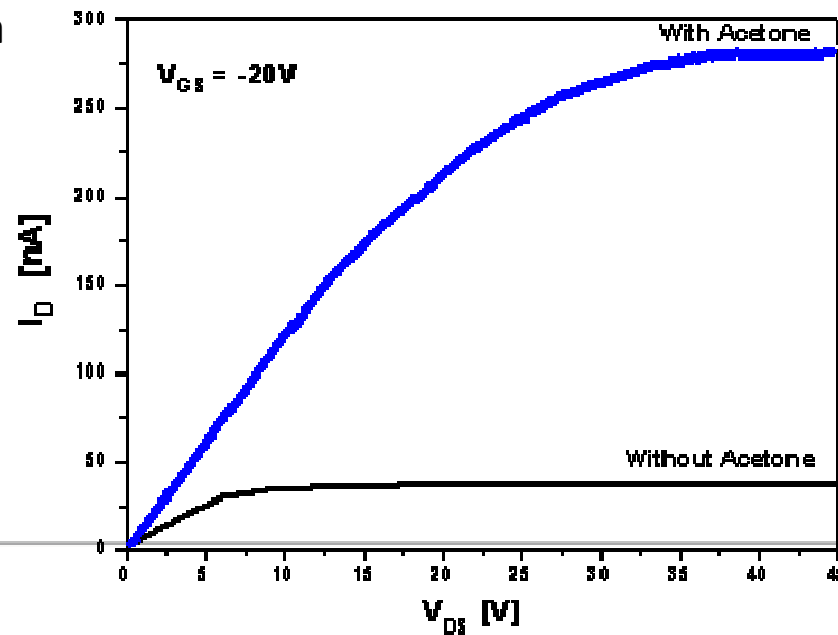
E. Guziewicz, M. Godlewski, and V. Osinniy

*Institute of Physics, Polish Academy of Sciences, Warsaw 02668, Poland*





S. Gierałtowska

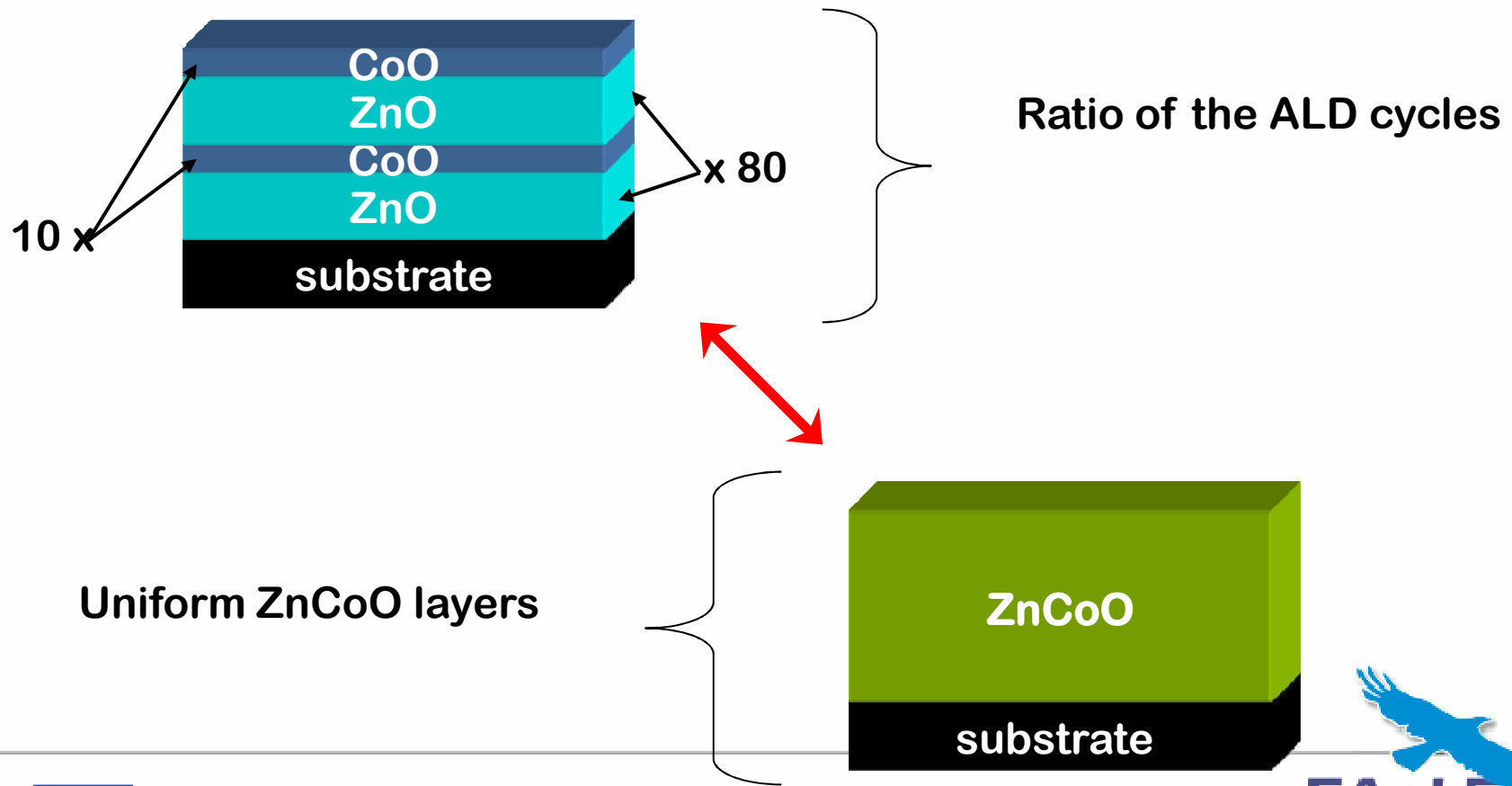


# Spintronics

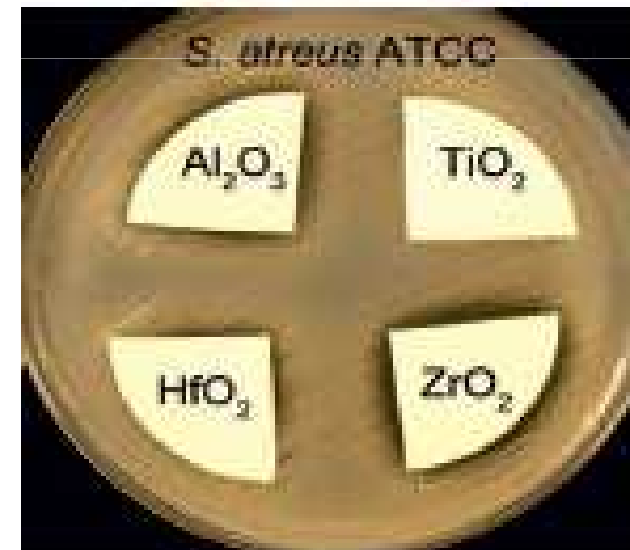
Uniformity of DMS samples  
- the most critical issue



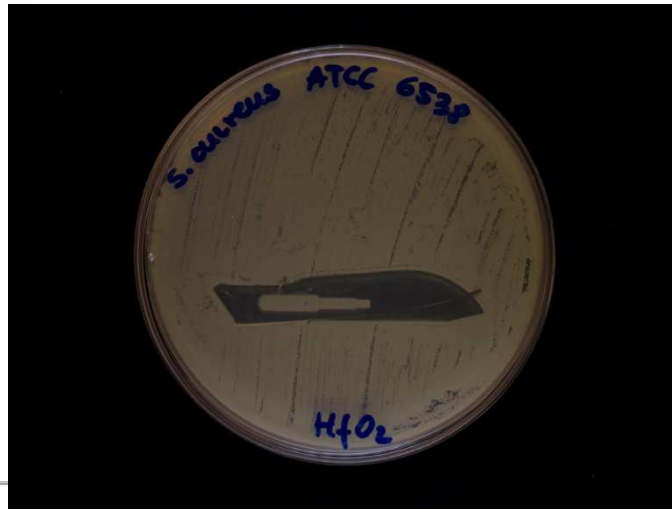
# Uniform Zn(Mn,Co)O layers by ALD



# Antibacterial coating



# Antibacterial coating

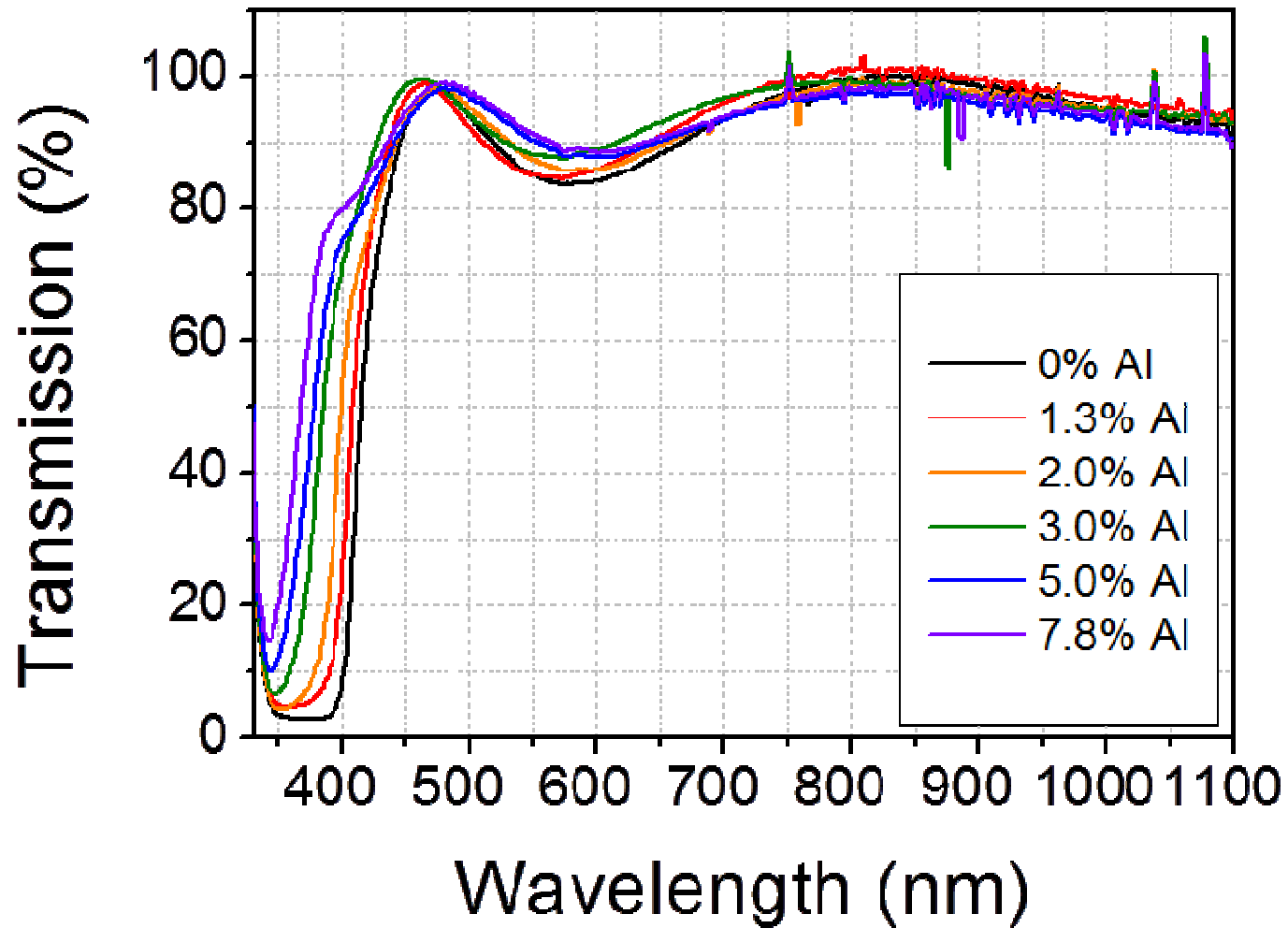


# Photovoltaics

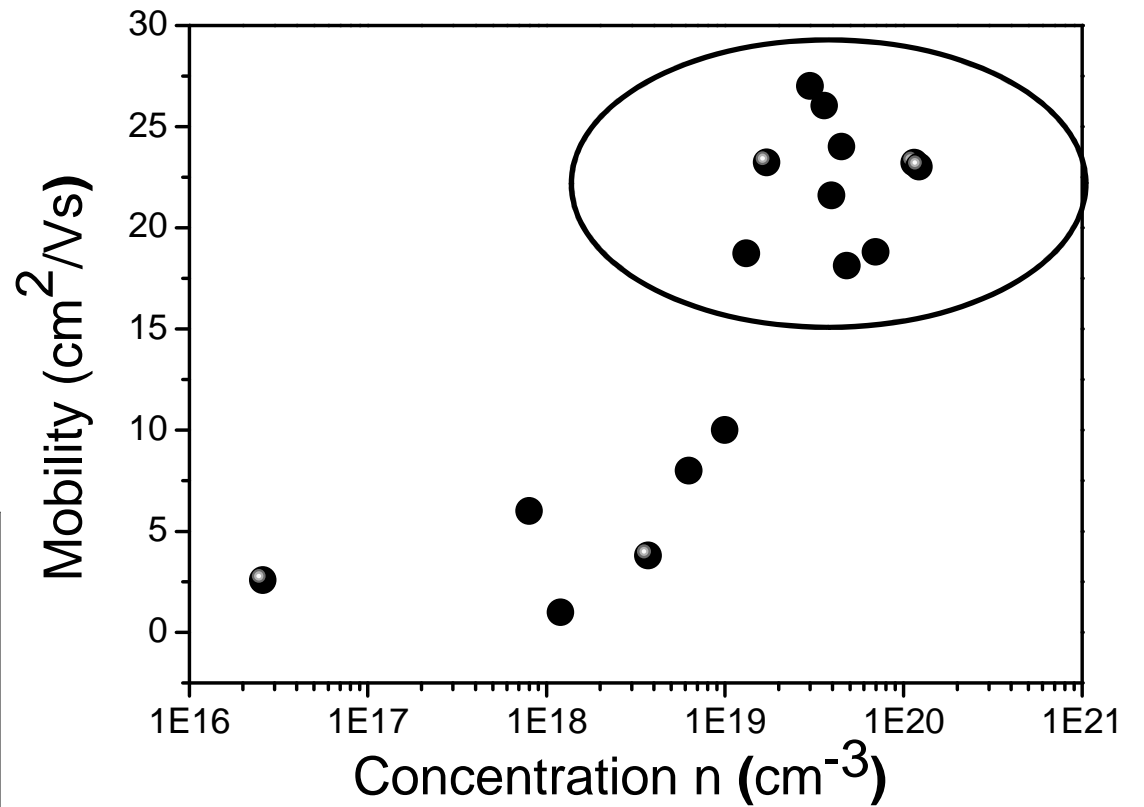
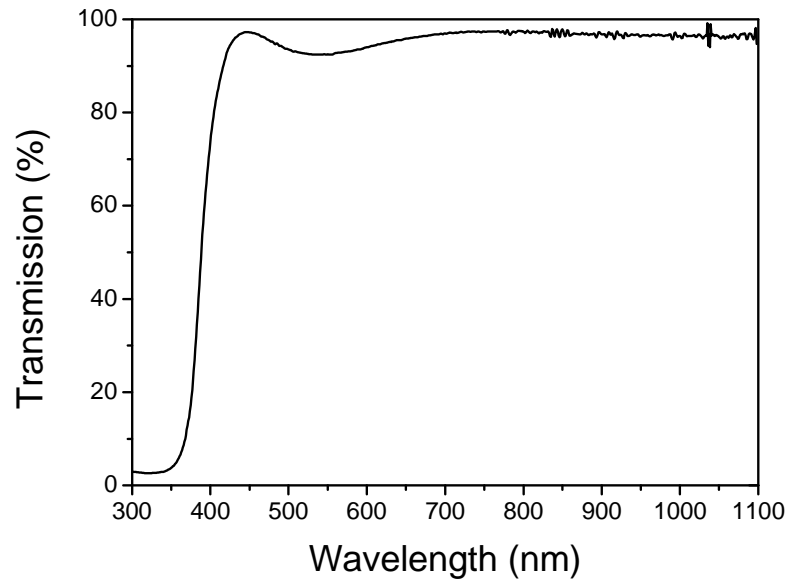
## TCO films based on ZnO:Al



G. Łuka



# ZnO TCO metodą ALD



G. Łuka, R. Pietruszka, Ł. Wachnicki



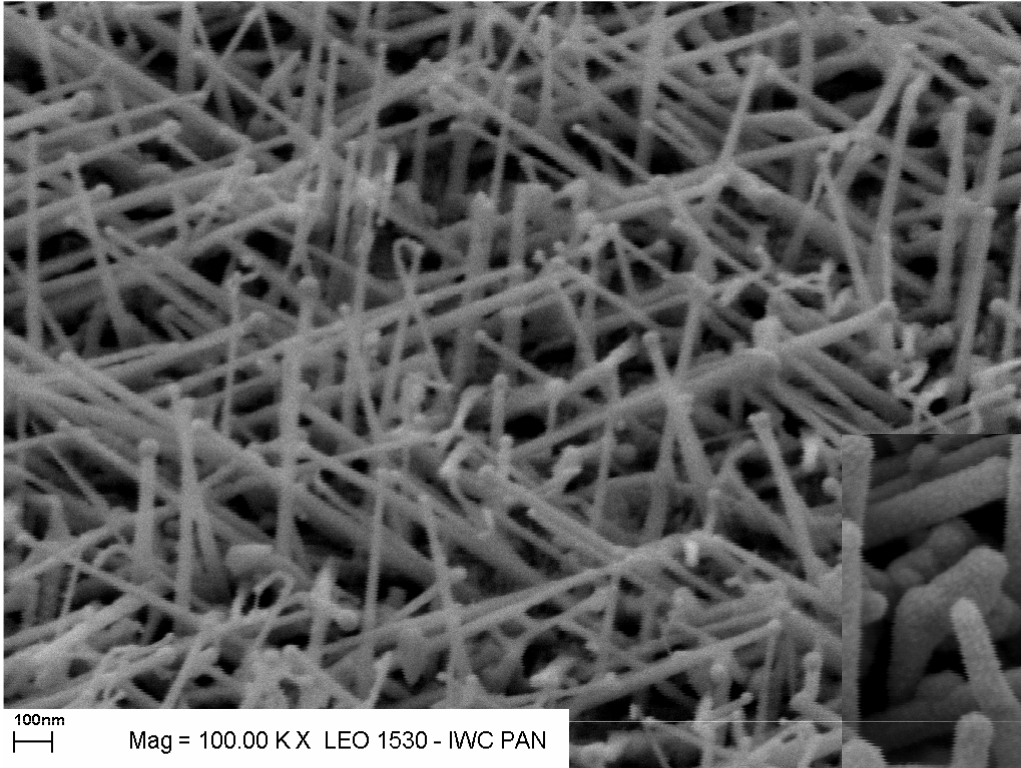
# Photovoltaics

## New architecture

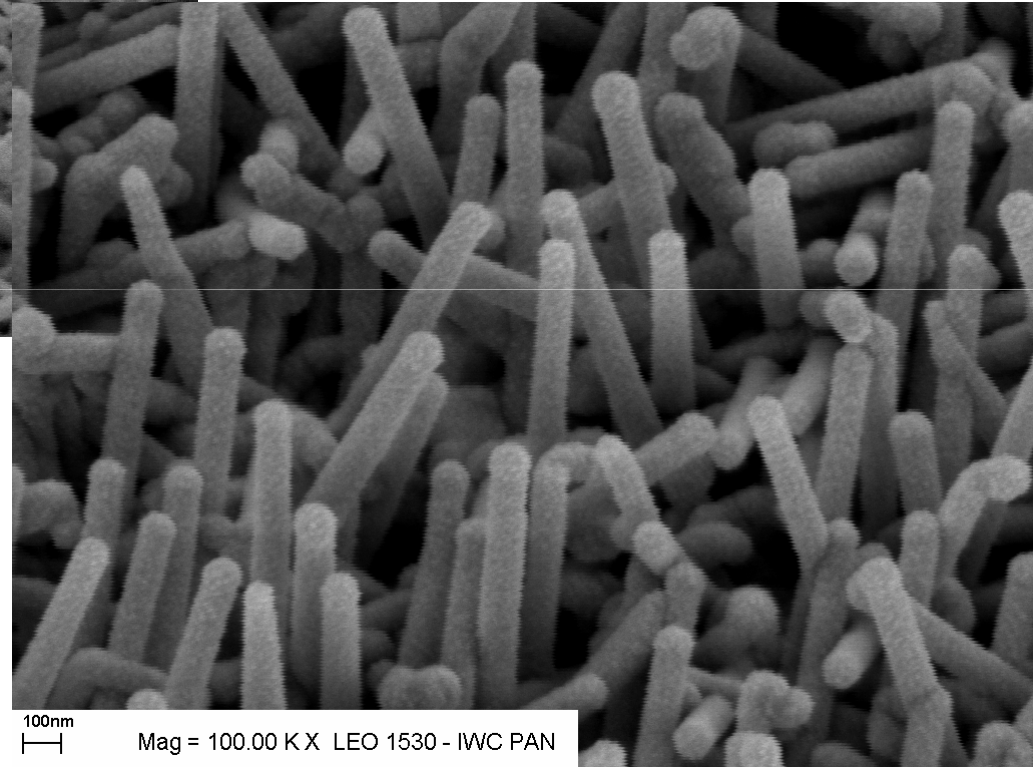


# Conformal coating of 3D structures- Nanowires of ZnTe coated with ZnO





← ZnTe nanowires on (100) oriented substrate

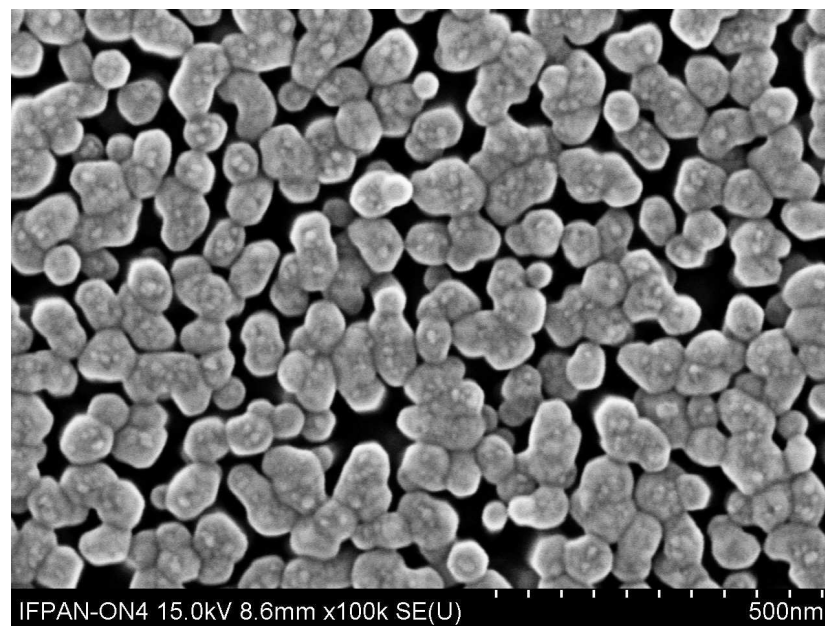
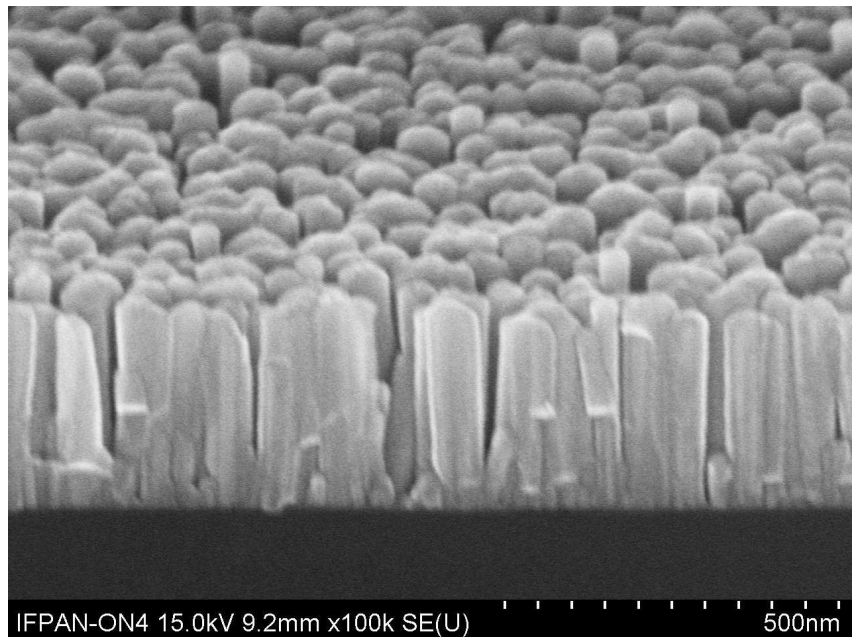


ZnO coated nanowires →

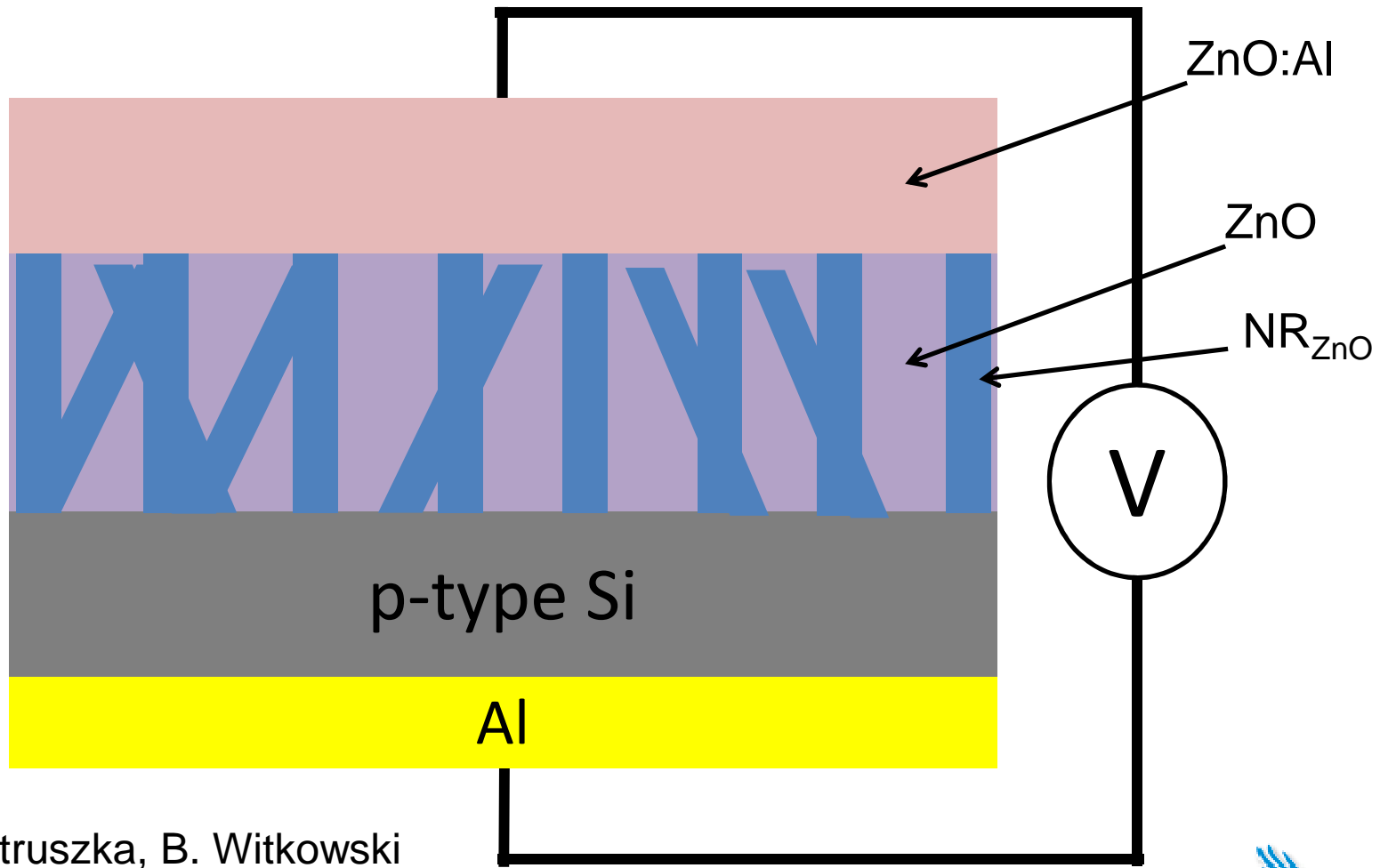
Ł. Wachnicki



## nanorods GaN on Si(111) coated with ZnO („shell” ALD)



Ł. Wachnicki



R. Pietruszka, B. Witkowski



# Marek Godlewski

## Summary:

1. Low temperature processes – range of hybrid structure possible
2. Conformal coating of developed surfaces – 3D structures
3. High quality of deposited material – High-k oxides with excellent properties



